

NPN General Pupose Amplifier

This device is designed for use as a medium power amplifier and switch requiring collector currents up to 500 mA.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	٥°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N4401	*MMBT4401	
PD	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

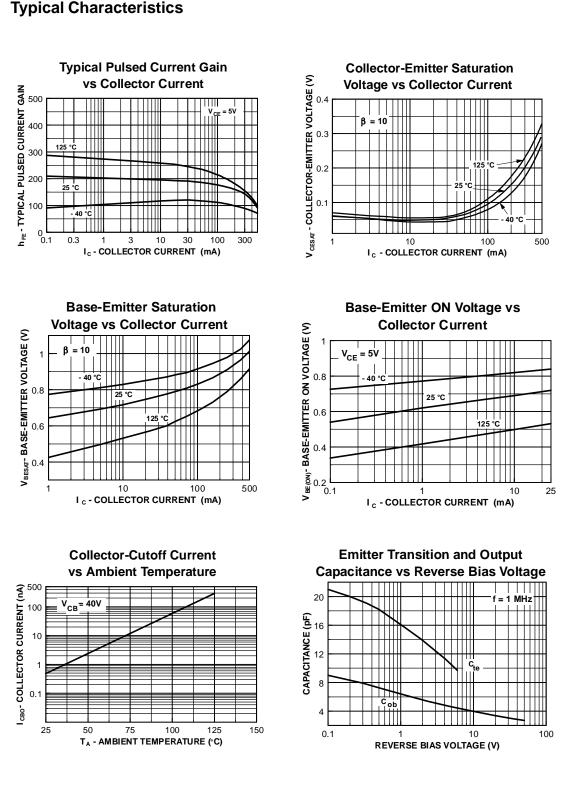
*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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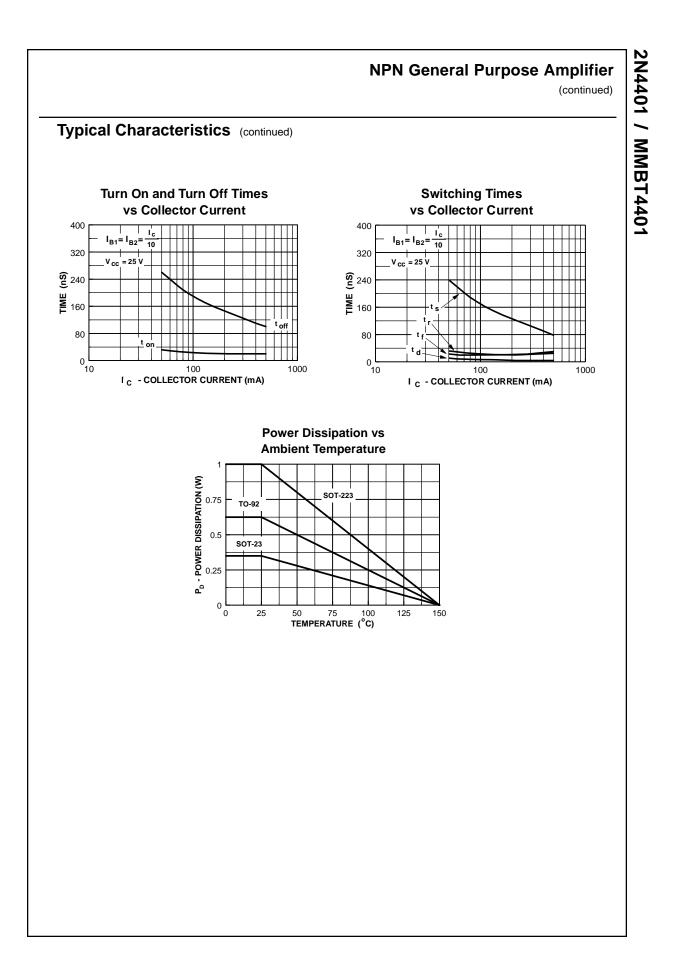
NPN General Purpose Amplifier (continued)

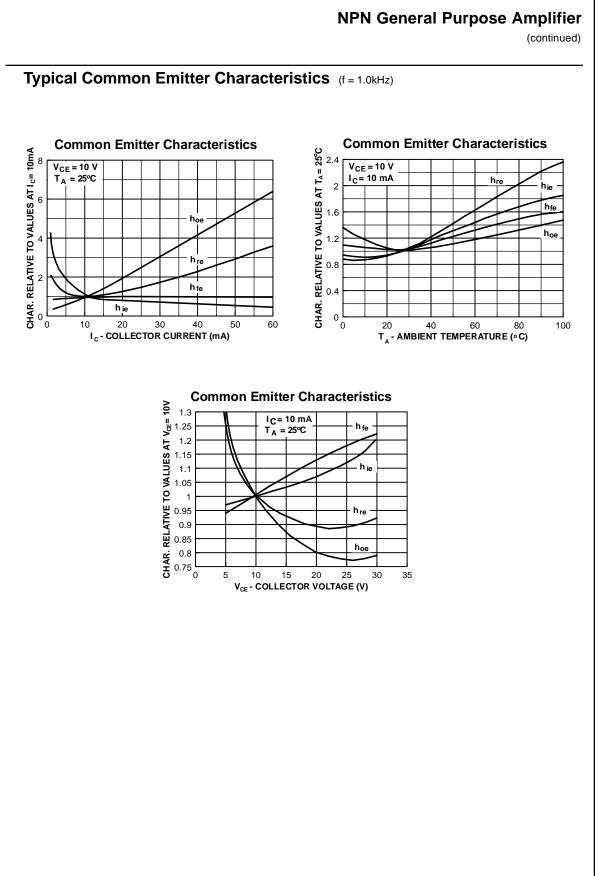
	Parameter	Test Conditions	Min	Мах	Units
	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 0.1 \text{ mA}, I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 0.1 {\rm mA}, I_{\rm C} = 0$	6.0		V
I _{BL}	Base Cutoff Current	V _{CE} = 35 V, V _{EB} = 0.4 V		0.1	μA
I _{CEX}	Collector Cutoff Current	$V_{CE} = 35 \text{ V}, \text{ V}_{EB} = 0.4 \text{ V}$		0.1	μA
ON CHAR	ACTERISTICS*				
	DC Current Gain	$I_{C} = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$	20		
		$I_{C} = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$	40		
		$I_{\rm C} = 10 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$	80	200	
		$I_{C} = 150 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	100 40	300	
/ _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 150 \text{ mA}, I_{\rm B} = 15 \text{ mA}$	10	0.4	V
()		$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$		0.75	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$	0.75	0.95 1.2	V V
r	Current Gain - Bandwidth Product Collector-Base Capacitance	$ I_{C} = 20 \text{ mA}, V_{CE} = 10 \text{ V}, \\ f = 100 \text{ MHz} \\ V_{CB} = 5.0 \text{ V}, I_{E} = 0, $		6.5	pF
Ceb Nie Nre	Emitter-Base Capacitance Input Impedance Voltage Feedback Ratio Small-Signal Current Gain Output Admittance		1.0 0.1 40 1.0	30 15 8.0 500 30	pF kΩ x 10 ⁻
Cob Ceb Nie Nre Nfe Noe SWITCHIN	Input Impedance Voltage Feedback Ratio Small-Signal Current Gain	$ \begin{array}{l} V_{BE} = 0.5 \ V, \ I_{C} = 0, \\ f = 140 \ \text{kHz} \\ I_{C} = 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f = 1.0 \ \text{kHz} \\ I_{C} = 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f = 1.0 \ \text{kHz} \\ I_{C} = 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ f = 1.0 \ \text{kHz} \\ I_{C} = 1.0 \ \text{mA}, \ V_{CE} = 10 \ V, \\ \end{array} $	0.1	15 8.0 500	kΩ x 10
Ceb Die Dre Dre SWITCHIN	Input Impedance Voltage Feedback Ratio Small-Signal Current Gain Output Admittance NG CHARACTERISTICS Delay Time	$\begin{split} V_{BE} &= 0.5 \text{ V}, \text{ I}_{C} = 0, \\ f &= 140 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 1.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ \end{split}$	0.1	15 8.0 500 30 15	kΩ x 10 μmhc

NPN General Purpose Amplifier (continued)



2N4401 / MMBT4401





2N4401 / MMBT4401

NPN General Purpose Amplifier

(continued)

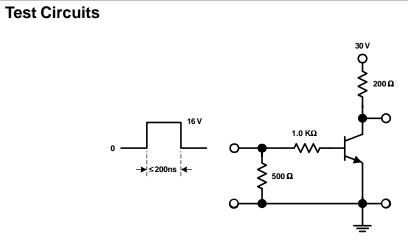


FIGURE 1: Saturated Turn-On Switching Timer

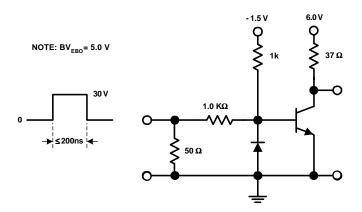


FIGURE 2: Saturated Turn-Off Switching Time



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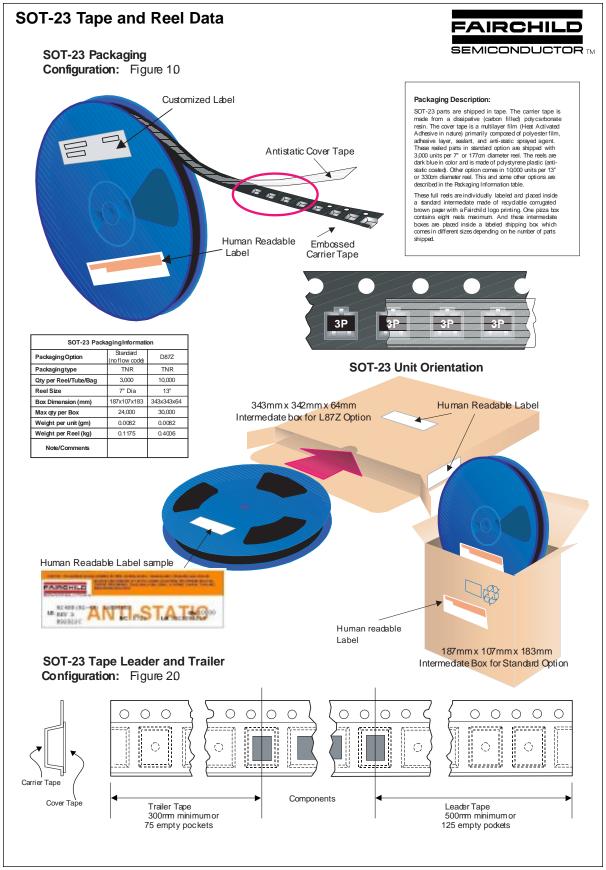
March 2001, Rev. B1





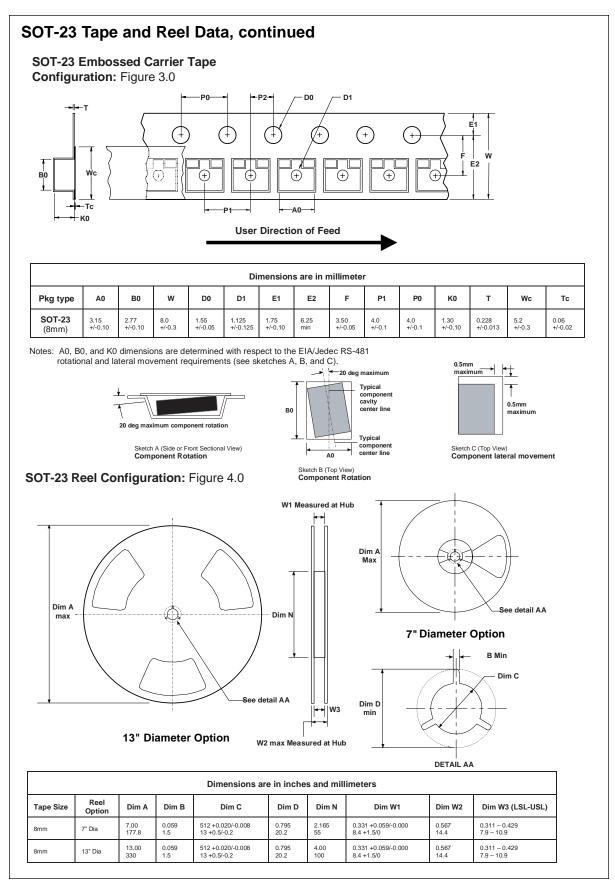
July 1999, Rev. A



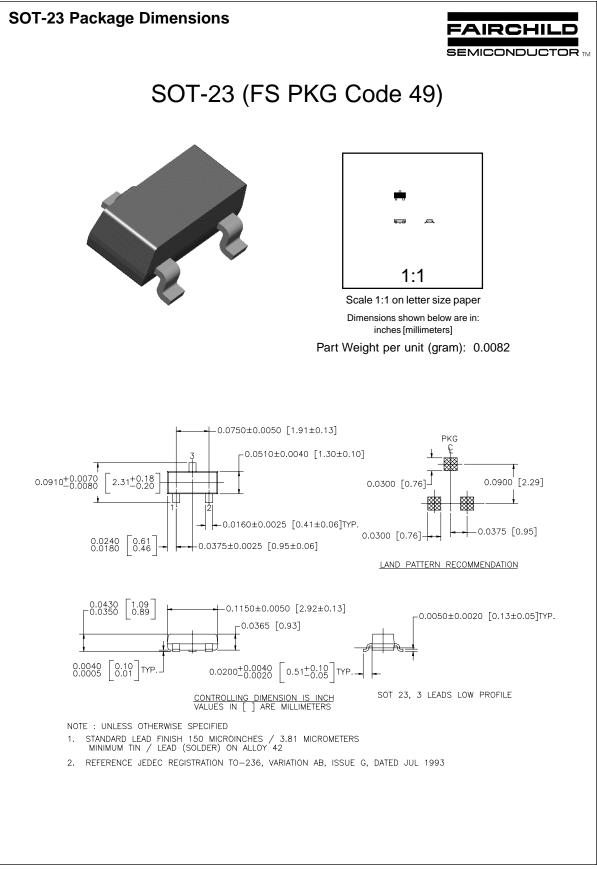


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